

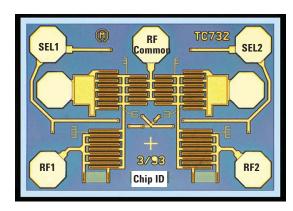
Agilent HMMC-2007 DC—8 GHz Terminated SPDT Switch

1GG7-8004

Data Sheet

Features

- Outputs terminated in 50 Ω when off
- Frequency range: DC to 8 GHz
- · Insertion loss: 1.2 dB @ 8 GHz
- Isolation:
 - > 70 dB @ 45 MHz
 - > 35 dB @ 8 GHz
- Return loss: 25 dB (both input and selected output)
 18 dB unselected output
- Switching speed:
 < 20 μs (10%–90% RF)
- P_{-1 dB}: 27 dBm
- · Harmonics (DC coupled):
 - < -80 dBc @ 10 dBm



Chip size: 660 x 960 µm (25.9 x 37.8 mils)

Chip size tolerance: $\pm 10 \mu m (\pm 0.4 mils)$

Chip thickness: $127 \pm 15 \mu m (5.0 \pm 0.6 \text{ mils})$ Pad dimensions: $120 \times 120 \mu m (4.7 \times 4.7 \text{ mils})$

Description

The HMMC-2007 is a GaAs monolithic microwave integrated circuit (MMIC) designed for low insertion loss and high isolation from DC to 8 GHz. It is intended for use as a general-purpose, single-pole, double-throw (SP-DT), absorptive switch. Two series and two shunt MESFETs per throw provide 1.4 dB maximum insertion loss and 38 dB typical isolation at 6 GHz. HMMC-2007 chips use through-substrate vias to provide ground connections to the chip backside and minimize the number of wire bonds required.

Absolute maximum ratings¹

Symbol	Parameters/conditions	Minimum	Maximum	Units
V_{sel}	Select voltages 1 & 2	-10.5	+10.5	Volts
P _{in}	RF input power		27	dBm
T _{op}	Operating temperature	– 55	+125	°C
T _{st}	Storage temperature	–65	+165	°C
T _{max}	Maximum assembly temperatu	ire	+200	°C
P _{unsel}	Power into unselected output		27	dBm

Operation in excess of any one of these ratings may result in permanent damage to this device. $T_A = 25$ °C except for T_{op} , T_{st} and T_{max} .



DC specifications/physical properties

 $(T_A = 25^{\circ}C)$

Symbol	Parameters/conditions	Minimum	Typical	Maximum	Units
I _{SEL -10V}	Leakage current @ –10V			200	μΑ
I _{SEL +10V}	Leakage current @ +10V			20	μΑ
V_p	Pinch-off voltage ($V_{SEL2} = V_p$, $V_{RFout2} = +2V$, $I_{RFout2} = 4$ mA, $V_{SEL1} = -10$ V, $V_{RFout1} =$ open circuit, $V_{RFin} =$ GND)	-6.75		-3.00	Volts
BV	Breakdown voltage (Test FET w/ $V_D = V_S = GND$, $I_G = -50 \mu A$)			-13.0	Volts

RF specifications
$$(T_{A}=25^{\circ}C,\,Z_{0}=50\,\,\Omega,\,V_{sel\text{-}high}=+10\,\,\text{V},\,V_{sel\text{-}low}=-10\,\,\text{V})$$

Symbol	Parameters/conditions	Minimum	Typical	Maximum	Units
BW	Guaranteed operating bandwidth	DC		8.0	GHz
IL	Insertion loss, RF _{in} to selected RF _{out} (ON throw), 6 GHz		1.1	1.4	dB
ISO	Isolation, RF _{in} to unselected RF _{out} (OFF throw), 6 GHz		38		dB
RL _{in}	Input return loss @ 6 GHz		25		dB
RL _{out-ON}	Output return loss, ON throw @ 6 GHz		25		dB
RL _{out-OFF}	Output return loss, OFF throw @ 6 GHz		18		dB
P _{-1 dB}	Input power where IL increases by 1 dB, $f_{in} = 2 \text{ GHz}$		27		dBm
t _s	Switching speed, 10%-90% RF envelope, f _{in} = 2 GHz	20		μs	

Applications

The HMMC-2007 can be used in instrumentation, communications, radar, ECM, EW, and many other systems requiring SPDT switching. It can be used for pulse modulation, port isolation, transfer switching, high-speed switching, replacement of mechanical switches, and so on.

Assembly techniques

GaAs MMICs are ESD sensitive. ESD preventive measures must be employed in all aspects of storage, handling, and assembly.

MMIC ESD precautions, handling considerations, die attach and bonding methods are critical factors in successful GaAs MMIC performance and reliability.

Agilent application note #54, "GaAs MMIC ESD, Die Attach and Bonding Guidelines" provides basic information on these subjects.

Additional references

AN #57, "FET Switch Speed and Settling Time."

S-Parameters¹ ($T_A = 25^{\circ}C$, $Z_0 = 50 \Omega$, V_{sel} high = +10 V, V_{sel} low = -10 V)

Frequency	S ₁₁			S ₂₁ (in	sertion	loss)	S31 (isolation)	S ₂₂ (01	l throw	<i>ı</i>)	S ₃₃ (OF	F throv	v)
(GHz)	dB	mag	ang	dB	mag	ang	dB	dB	mag	ang	dB	mag	ang
0.5	-26.41	0.048	- 57.11	-1.08	0.88	-49.06	-67.74	-28.40	0.03	-47.94	-32.26	0.024	47.18
1.0	-27.53	0.042	-113.83	-1.13	0.88	-93.69	-60.55	-24.74	0.05	-117.54	-30.79	0.029	-38.11
1.5	-30.69	0.029	-176.73	-1.18	0.87	-138.08	-56.17	-31.91	0.02	168.76	-30.35	0.030	-64.68
2.0	-32.37	0.024	115.57	-1.21	0.87	177.39	-53.18	-31.31	0.02	119.22	-26.21	0.049	-134.70
2.5	-31.79	0.026	61.35	-1.25	0.87	133.00	-50.38	-28.90	0.03	68.41	-26.38	0.048	151.66
3.0	-30.60	0.030	4.27	-1.30	0.86	88.53	-47.63	-32.95	0.02	-11.68	-25.66	0.052	103.24
3.5	-28.53	0.037	-58.32	-1.33	0.86	44.08	-45.67	-29.26	0.03	-44.21	-22.99	0.071	38.61
4.0	-27.14	0.044	-124.01	-1.34	0.86	-0.53	-44.12	-30.61	0.02	-113.40	-22.41	0.076	-21.25
4.5	-26.46	0.048	172.69	-1.37	0.85	-45.16	-42.68	-32.21	0.02	165.53	-21.68	0.082	-75.25
5.0	-27.03	0.045	107.19	-1.40	0.85	-89.79	-41.45	-36.49	0.01	141.98	-19.88	0.101	-133.81
5.5	-28.64	0.037	32.44	-1.42	0.85	-134.56	-40.28	-34.51	0.01	4.26	19.89	0.101	167.02
6.0	-29.55	0.033	-59.18	-1.45	0.85	-179.46	-39.16	-32.44	0.02	-100.27	-19.03	0.112	115.49
6.5	-26.88	0.045	-156.32	-1.51	0.84	135.54	-38.12	-27.18	0.04	176.54	-18.28	0.122	56.80
7.0	-23.24	0.069	130.95	-1.56	0.84	90.76	-37.13	-23.83	0.06	122.00	-18.67	0.117	-2.63
7.5	-21.53	0.084	70.91	-1.52	0.84	46.04	-36.36	-21.48	0.08	51.31	-18.61	0.117	-60.32
8.0	-21.21	0.087	15.06	-1.62	0.83	0.47	-35.64	-21.73	0.08	-15.06	-17.65	0.131	-124.25
8.5	-20.92	0.090	-41.26	-1.64	0.83	-44.44	-34.83	-22.22	0.07	-81.88	-16.95	0.142	172.46
9.0	-19.88	0.101	-104.30	-1.66	0.83	-90.23	-34.13	-20.42	0.09	-145.01	-16.07	0.157	115.03
9.5	-18.65	0.117	-175.05	-1.84	0.81	-135.81	-33.62	-18.17	0.12	145.14	-14.94	0.179	59.82
10.0	-17.04	0.141	116.96	-1.90	0.80	179.24	-34.14	-16.31	0.15	85.15	-14.31	0.193	3.39

¹ Three-port wafer-probed data: Port 1 = RF input, Port 2 = selected RF output (i.e., ON throw), and Port 3 = unselected RF output (i.e., OFF throw).

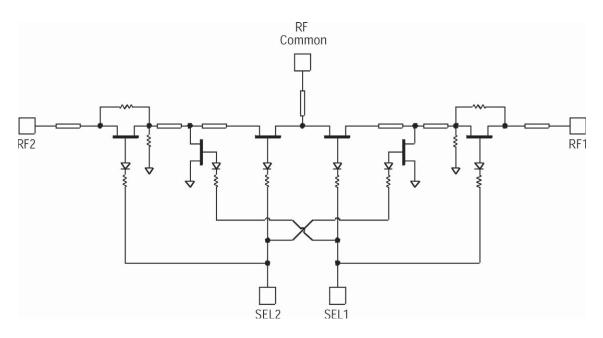


Figure 1. Schematic

Select line		RF path	RF path				
SEL1	SEL2	RF IN to RF OUT2	RF IN to RF OUT1				
+10 V	-10 V	Isolated	Low loss				
-10 V	+10 V	Low loss	Isolated				

Figure 2. Recommended operating conditions (T $_{\!A}=25^{\circ}\text{C}\text{)}$

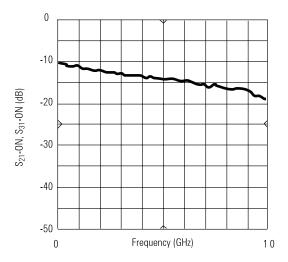


Figure 3. Insertion Loss¹

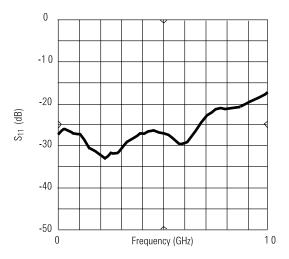


Figure 5. Input return loss¹

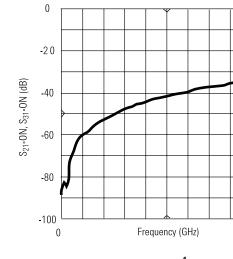
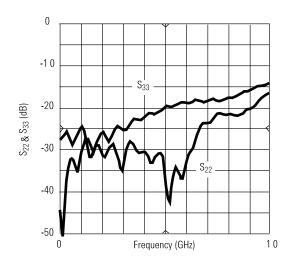


Figure 4. Input-to-output Isolation¹



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Figure 6. Output return loss¹

¹ Data taken with the device mounted in modular breadboard package

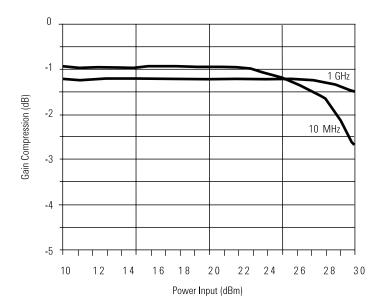


Figure 7. Gain compression

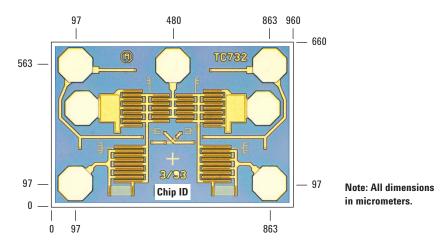


Figure 5. Bonding pad locations

Note:

All compression data measured on individual device mounted in an Agilent 83040 Series Modular Microcircuit Package @ $T_{case} = 25^{\circ}C$.

This data sheet contains a variety of typical and guaranteed performance data. The information supplied should not be interpreted as a complete list of circuit specifications. Customers

considering the use of this, or other Agilent GaAs ICs, for their design should obtain the current production specifications from Agilent. In this data sheet the term typical refers to the 50th percentile performance. For additional information contact Agilent MMIC_Helpline@agilent.com.

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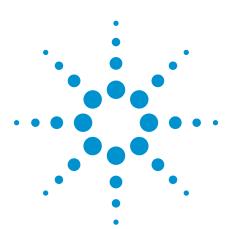
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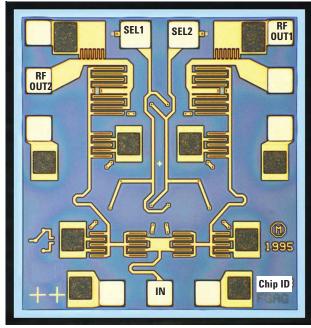
Agilent HMMC-2027 DC-26.5 GHz SPDT GaAs MMIC Switch

1GG7-8005

Data Sheet

Features

- Outputs terminated in 50 Ω when off
- Frequency range: DC to 26.5 GHz
- Insertion loss: 2.5 dB @ 26.5 GHz
- Isolation: > 70 dB @ 45 MHz
 30 dB @ 26.5 GHz
- Return loss: 15 dB (both input and selected output)
 12 dB unselected output
- Switching speed:< 1 ns (10%–90% RF)
- P_{-1 dB}: 18 dBm @ 10 MHz
 27 dBm @ 2 GHz
- Harmonics (DC coupled):
 - < -45 dBc @ 10 MHz and 5 dBm
 - < -65 dBc @ 2 GHz and 5 dBm



Chip size: 900 x 960 µm (35.4 x 37.8 mils)

Chip size tolerance: ±10 µm (±0.4 mils)

Chip thickness: $127 \pm 15 \mu m (5.0 \pm 0.6 \text{ mils})$ Pad dimensions: $80 \times 80 \mu m (3.2 \times 3.2 \text{ mils})$ or larger

Description

The HMMC-2027 is a GaAs monolithic microwave integrated circuit (MMIC) designed for low insertion loss and high isolation from DC to 26.5 GHz. It is intended for use as a general-purpose, single-pole, double-throw (SP-DT), absorptive switch. Two series and two shunt MESFETs per throw provide 3 dB maximum insertion loss and 30 dB minimum isolation at 26.5 GHz. HMMC-2027 chips use through-substrate vias to provide ground connections to the chip backside and minimize the number of wire bonds required.

Absolute maximum ratings¹

Symbol	Parameters/conditions	Minimum	Maximum	Units
$V_{\rm sel}$	Select voltages 1 & 2	-10.5	+3	Volts
P _{in}	RF input power		25	dBm
T _{op}	Operating temperature	- 55	+125	°C
T _{st}	Storage temperature	-65	+165	°C
T _{max}	Maximum assembly temperatur	+200	°C	
P _{unsel} ²	Power into unselected output		15	dBm

¹ Operation in excess of any one of these ratings may result in permanent damage to this device. $T_A = 25^{\circ}\text{C}$ except for T_{op} , $T_{st'}$ and T_{max} .

² Operation in excess of these @ T_{op-max} may result in permanent damage.



DC specifications/physical properties

 $(T_A = 25^{\circ}C)$

Symbol	Parameters/conditions	Minimum	Typical	Maximum	Units
I _I	Leakage current @ -10 V			200	μА
V_p	Pinch-off voltage ($V_{SEL2} = V_p$, $V_{RFout2} = +2V$, $I_{RFout2} = 2$ mA, $V_{SEL1} = -10$ V, $V_{RFout1} = $ open circuit, $V_{RFin} = $ GND)	-6.75		-3.00	Volts
BV_{gss}	Breakdown voltage (Test FET w/ $V_D = V_S = GND$, $I_G = -50 \mu A$)			-13.0	Volts

RF specifications
$$(T_{A}=25^{\circ}\text{C},\,Z_{0}=50\,\,\Omega,\,V_{sel\text{-}high}=0\,\,\text{V},\,V_{sel\text{-}low}=-10\,\,\text{V})$$

Symbol	Parameters/conditions	Minimum	Typical	Maximum	Units
BW	Guaranteed operating bandwidth	DC		26.5	GHz
IL	Insertion loss, RF _{in} to selected RF _{out} (ON throw), 26.5 GHz		2.5	3.0	dB
ISO	Isolation, RF _{in} to unselected RF _{out} (OFF throw), 26.5 GHz	27	30		dB
ISO	Isolation, RF _{in} to unselected RF _{out} (OFF throw), 18 GHz	40	43		dB
RL _{in}	Input return loss	12	15		dB
RL _{out-ON}	Output return loss, ON throw	13	16		dB
RL _{out-OFF}	Output return loss, OFF throw	9	12		dB
P _{-1 dB}	Input power where IL increases by 1 dB, $f_{in} = 2 \text{ GHz}$		27		dBm
t _s	Switching speed, 10%-90% RF envelope, f _{in} = 2 GHz		1		ns

Applications

The HMMC-2027 can be used in instrumentation, communications, radar, ECM, EW, and many other systems requiring SPDT switching. It can be used for pulse modulation, port isolation, transfer switching, high-speed switching, replacement of mechanical switches, and so on.

Assembly techniques

GaAs MMICs are ESD sensitive. ESD preventive measures must be employed in all aspects of storage, handling, and assembly.

MMIC ESD precautions, handling considerations, die attach and bonding methods are critical factors in successful GaAs MMIC performance and reliability.

Application note #54, "GaAs MMIC ESD, Die Attach and Bonding Guidelines" provides basic information on these subjects.

Additional references

AN #57, "FET Switch Speed and Settling Time."

S-Parameters¹ ($T_A = 25^{\circ}C$, $Z_0 = 50 \Omega$, V_{sel} high = 0 V, V_{sel} low = -10 V)

Frequency	S ₁₁			S ₂₁ (in	sertion	loss)	S31 (isolation)	S ₂₂ (01	\ throw	v)	S ₃₃ (OF	F thro	w)
(GHz)	dB	M	ang	dB	M	ang	dB	dB	M	ang	dB	M	ang
0.5	-18.28	0.12	-7.04	-1.33	0.86	-8.52	-71.40	-18.44	0.12	-9.89	-16.79	0.14	173.87
1.5	-18.53	0.12	-13.70	-1.35	0.86	-14.62	-61.02	-18.46	0.12	-19.75	-16.47	0.15	171.75
4.0	-18.92	0.11	-27.64	-1.41	0.85	-24.53	-51.67	-18.75	0.12	-38.78	-15.36	0.17	168.03
6.5	-19.43	0.11	-45.02	-1.47	0.84	-39.56	-49.50	-19.10	0.11	-63.22	-14.55	0.19	152.55
9.0	-20.57	0.09	-64.07	-1.56	0.84	-55.13	-46.87	-19.72	0.10	15.79	-14.28	0.19	136.68
11.5	-21.85	0.08	-2.59	-1.62	0.83	-71.03	-44.71	-20.91	0.09	243.63	-13.84	0.20	121.81
14.0	-23.10	0.07	258.44	-1.74	0.82	-29.63	-42.30	-22.41	0.08	217.48	-13.53	0.21	106.44
16.5	-24.05	0.06	235.82	-1.88	0.81	258.60	-41.74	-24.17	0.06	179.74	-12.95	0.23	92.94
19.0	-24.59	0.06	224.56	-1.99	0.80	242.13	-37.07	-27.09	0.04	133.20	-12.76	0.23	74.01
21.5	-25.42	0.05	206.39	-2.10	0.79	227.84	-40.39	-28.85	0.04	68.10	-13.12	0.22	68.84
24.0	-24.66	0.06	209.77	-2.10	0.78	209.72	-34.46	-24.31	0.06	6.26	-12.11	0.25	54.32
26.5	-21.90	0.08	223.86	-2.39	0.76	191.82	-31.38	-19.43	0.11	-33.31	-12.03	0.25	3

¹ Three-port wafer-probed data: Port 1 = RF input, Port 2 = selected RF output (i.e., ON throw), and Port 3 = unselected RF output (i.e., OFF throw).

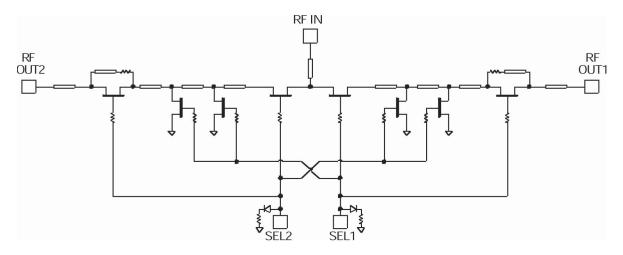


Figure 1. Schematic

Select line		RF path	RF path				
SEL1	SEL2	RF IN to RF OUT1	RF IN to RF OUT2				
-10 V	0 V	Isolated	Low loss				
0 V	-10 V	Low loss	Isolated				

Figure 2. Recommended operating conditions (T $_{\!A}=25^{\circ}\text{C}\text{)}$

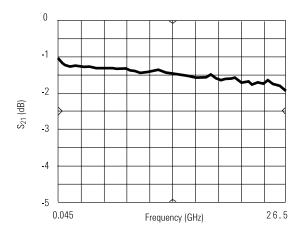


Figure 3. Insertion loss¹

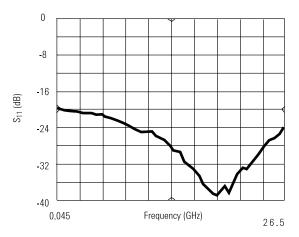


Figure 5. Input return loss¹

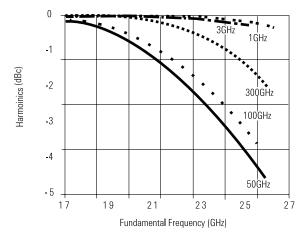


Figure 7. Gain compression²

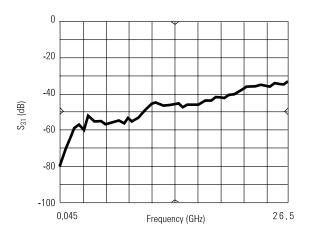


Figure 4. Input-to-output isolation¹

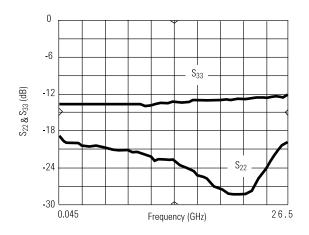


Figure 6. Output return loss¹

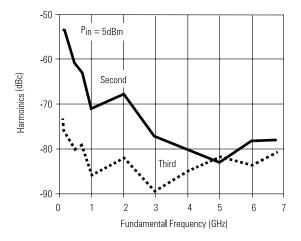


Figure 8. Harmonics^{2, 3}

- 1 Data obtained from wafer-probed measurements.
- 2 All compression and harmonic data measured on individual device mounted in an Agilent 83040 Series Modular Microcircuit Package @ T_{case} = 25°C.
- 3 Harmonic data points below –80 dBc are at or near the noise floor of the measurement system.

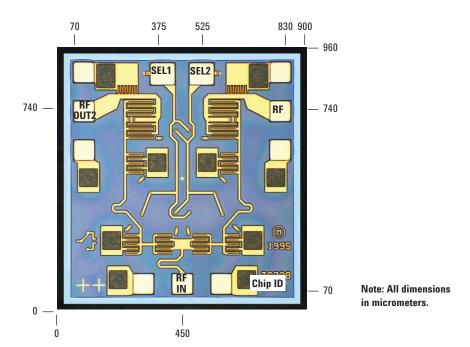


Figure 9. Bonding pad positions

This data sheet contains a variety of typical and guaranteed performance data. The information supplied should not be interpreted as a complete list of circuit specifications. Customers

considering the use of this, or other Agilent GaAs ICs, for their design should obtain the current production specifications from Agilent. In this data sheet the term typical refers to the 50th percentile performance. For additional information contact Agilent MMIC_Helpline@agilent.com.

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